

ON Semiconductor®

# RHRG5060-F085 50A, 600V Hyperfast Rectifier

#### **Features**

- High Speed Switching (  $t_{rr}$ =45ns(Typ.) @  $I_F$ =50A )
- Low Forward Voltage(V<sub>F</sub>=1.67V(Typ.) @ I<sub>F</sub>=50A)
- · Avalanche Energy Rated
- AEC-Q101 Qualified

### **Applications**

- · Switching Power Supply
- · Power Switching Circuits
- · General Purpose
- · Automotive and General Purpose

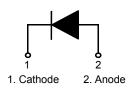
## Max Ratings (600V, 50A)

The RHRG5060-F085 is an Hyperfast™ diode with soft recovery characteristics (trr < 45ns). It has half the recovery time of ultrafast diode and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of automotive switching power supplies and other power switching automotive applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

### **Pin Assignments**





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	600	V	
V <sub>RWM</sub>	Working Peak Reverse Voltage	600	V	
V <sub>R</sub>	DC Blocking Voltage	600	V	
I <sub>F(AV)</sub>	Average Rectified Forward Current @ T <sub>C</sub> = 25°C	50	Α	
I <sub>FSM</sub>	Non-repetitive Peak Surge Current (Halfwave 1 Phase 50Hz)	150	А	
E <sub>AVL</sub>	Avalanche Energy (1.4A, 40mH)	40	mJ	
T <sub>J,</sub> T <sub>STG</sub>	Operating Junction and Storage Temperature	- 55 to +175	°C	

### Thermal Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	0.42	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	45	°C/W

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Tube	Quantity
RHRG5060	RHRG5060-F085	TO-247	1	30

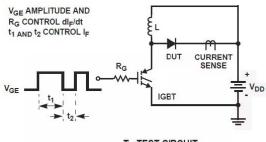
# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions		Min.	Тур.	Max	Units
I <sub>R</sub>	Instantaneous Reverse Current	V <sub>R</sub> = 600V	T <sub>C</sub> = 25 °C	-	-	250	uA
			T <sub>C</sub> = 175 °C	-	-	1.5	mA
V <sub>FM</sub> <sup>1</sup>	Instantaneous Forward Voltage	I <sub>F</sub> = 50A	T <sub>C</sub> = 25 °C T <sub>C</sub> = 175 °C	-	1.67 1.29	2.1 1.7	V V
t <sub>rr</sub> <sup>2</sup>	Reverse Recovery Time	$I_F$ =1A, di/dt = 100A/ $\mu$ s, V <sub>CC</sub> = 390V	T <sub>C</sub> = 25 °C	-	37	45	ns
		$I_F$ =50A, di/dt = 100A/ $\mu$ s, $V_{CC}$ = 390V	T <sub>C</sub> = 25 °C T <sub>C</sub> = 175 °C	-	45 200	60 -	ns ns
t <sub>a</sub> t <sub>b</sub>	Reverse Recovery Time	$I_F$ =50A, di/dt = 100A/ $\mu$ s, $V_{CC}$ = 390V	T <sub>C</sub> = 25 °C	-	25 20	-	ns ns
$Q_{rr}$	Reverse Recovery Charge			-	45	-	nC

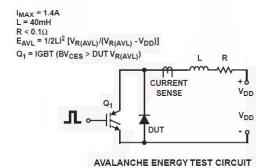
#### Notes:

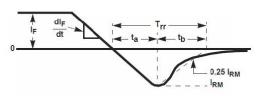
- 1. Pulse : Test Pulse width =  $300\mu s$ , Duty Cycle = 2%
- 2. Guaranteed by design

### **Test Circuit and Waveforms**

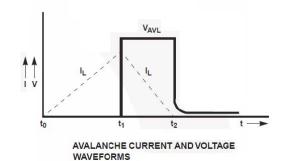


T<sub>rr</sub> TEST CIRCUIT





Trr WAVEFORMS AND DEFINITIONS



# **Typical Performance Characteristics**

Figure 1. Typical Forward Voltage Drop vs. Forward Current

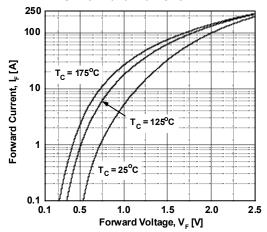


Figure 3. Typical Junction Capacitance

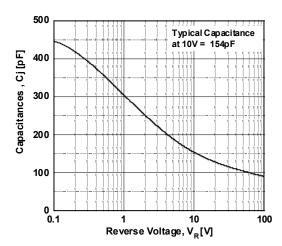


Figure 5. Typical Reverse Recovery Current vs. di/dt

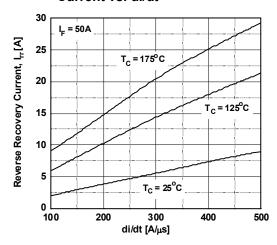


Figure 2. Typical Reverse Current vs.

Reverse Voltage

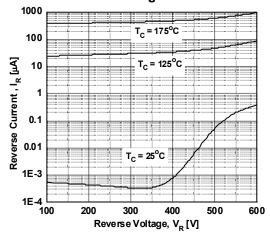


Figure 4. Typical Reverse Recovery Time vs. di/dt

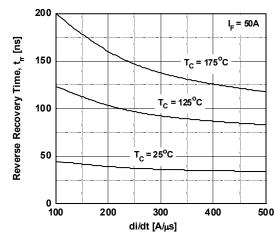
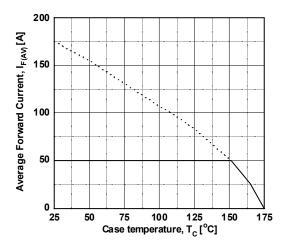


Figure 6. Forward Current Derating Curve



# **Typical Performance Characteristics** (Continued)

Figure 7. Reverse Recovery Charge

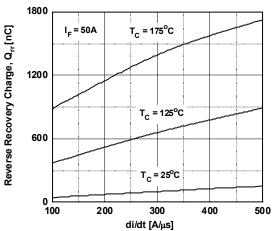
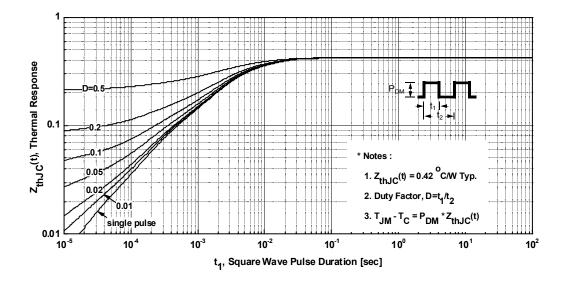
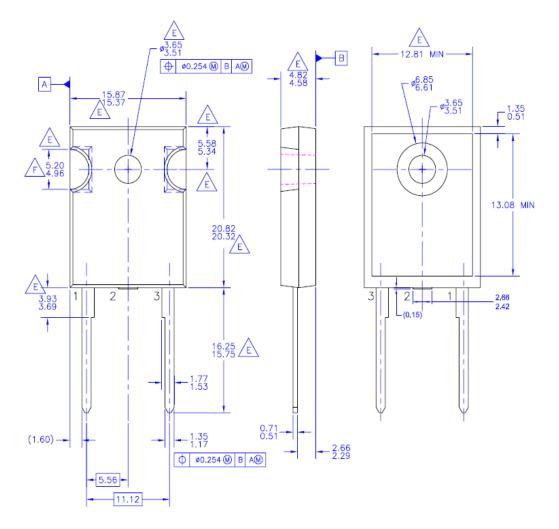


Figure 8. Transient Thermal Response Curve



### **Mechanical Dimensions**

# TO-247-2L



#### NOTES: UNLESS OTHERWISE SPECIFIED

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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
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Dimensions in Millimeters

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